FK6K0201

Silicon N-channel MOS FET

For switch circuits

■ Overview

FK6K0201 is N-channel signal type MOS FET employed small size surface mounting package.

■ Features

- Low drain-source ON resistance: $R_{DS(on)}$ typ. = 13 mΩ (V_{GS} = 4.5 V)
- High-speed switching
- Small size surface mounting package: WSMini6-F1-B
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	20	V
Gate-source surrender voltage	V_{GSS}	±10	V
Drain current	I_D	4.5	A
Peak drain current *1	I_{DP}	18	A
Power dissipation *2	P_D	700	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

Note) *1: t = 10 μs, Duty cycle < 1%

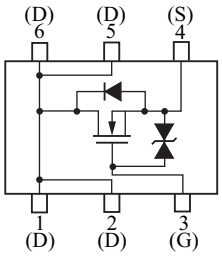
*2: Measuring on glass epoxy board (25.4 mm × 25.4 mm × t0.8 mm) coated with which has more than 300mm^2.
Absolute maximum rating without heat sink for P_D is 150 mW

■ Package

- Code
  WSMini6-F1-B
- Pin Name
  1: Drain 4: Source
  2: Drain 5: Drain
  3: Gate 6: Drain

■ Marking Symbol: TA

■ Internal Connection

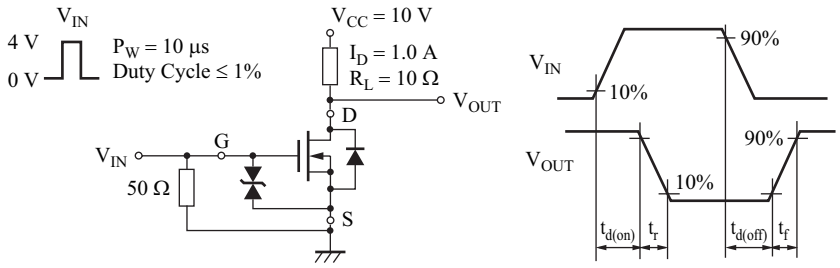


■ Electrical Characteristics T_a = 25°C±3°C

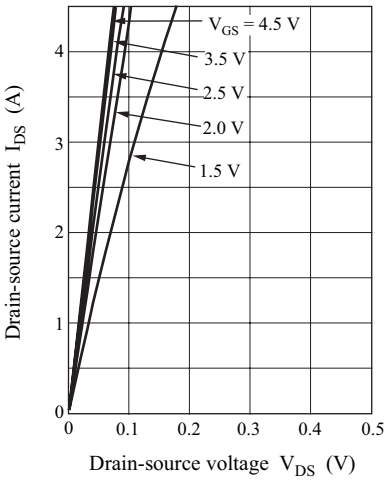
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	I_D = –1.0 mA, V_{GS} = 0	20			V
Drain-source cutoff current	I_{DSS}	V_{DS} = –10 V, V_{GS} = 0			1.0	μA
Gate-source cutoff current	I_{GSS}	V_{GS} = ±8 V, V_{DS} = 0			±10	μA
Gate threshold voltage	V_{TH}	I_D = –1.0 mA, V_{DS} = –6.0 V	0.4	0.85	1.3	V
Drain-source ON resistance	$R_{DS(on)}$	I_D = 2.0 A, V_{GS} = 4.5 V		13	17.5	mΩ
		I_D = 1.0 A, V_{GS} = 2.5 V		16	28	
Forward transfer admittance	$\|Y_{fs}\|$	I_D = 1.0 A, V_{DS} = 10 V	3.0			S
Short-circuit input capacitance (Common source)	C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz		1 730		pF
Short-circuit output capacitance (Common source)	C_{oss}			155		pF
Reverse transfer capacitance (Common source)	C_{rss}			150		pF
Turn-on delay time *	$t_{d(on)}$	V_{DD} = 10 V, V_{GS} = 0 V to 4 V, I_D = 1.0 A		19		ns
Rise time *	t_r			30		ns
Turn-off delay time *	$t_{d(off)}$			150		ns
Fall time *	t_f			75		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

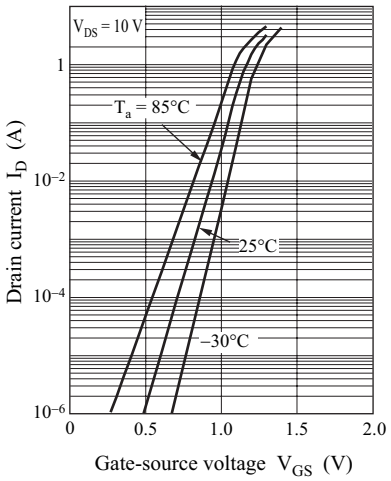
2. *: t_{on} , t_{off} measurement circuit



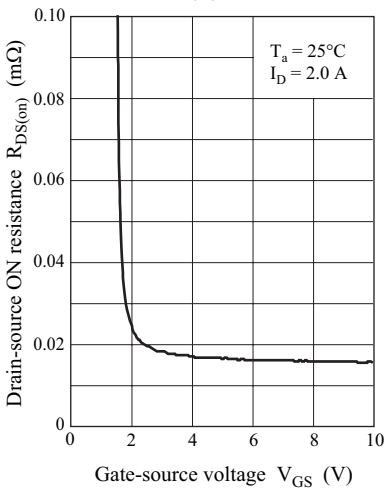
I_{DS} — V_{DS}



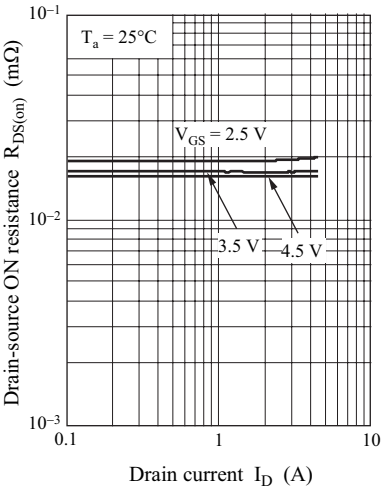
I_D — V_{GS}



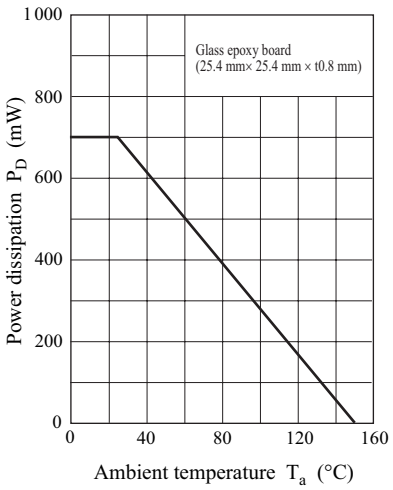
$R_{DS(on)}$ — V_{GS}



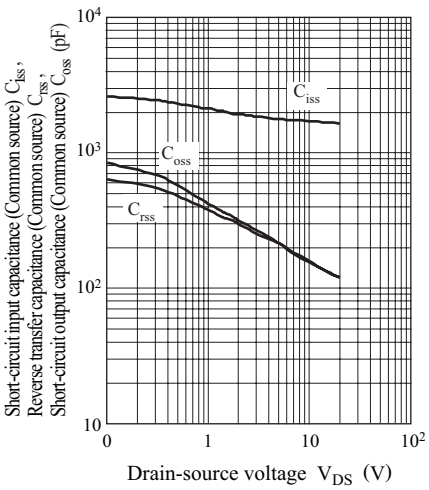
$R_{DS(on)}$ — I_D



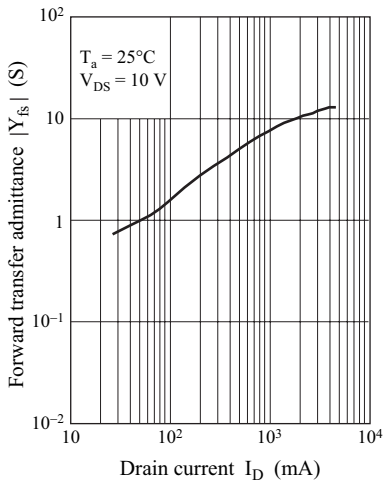
P_D — T_a



C_{iss} , C_{rss} , C_{oss} — V_{DS}

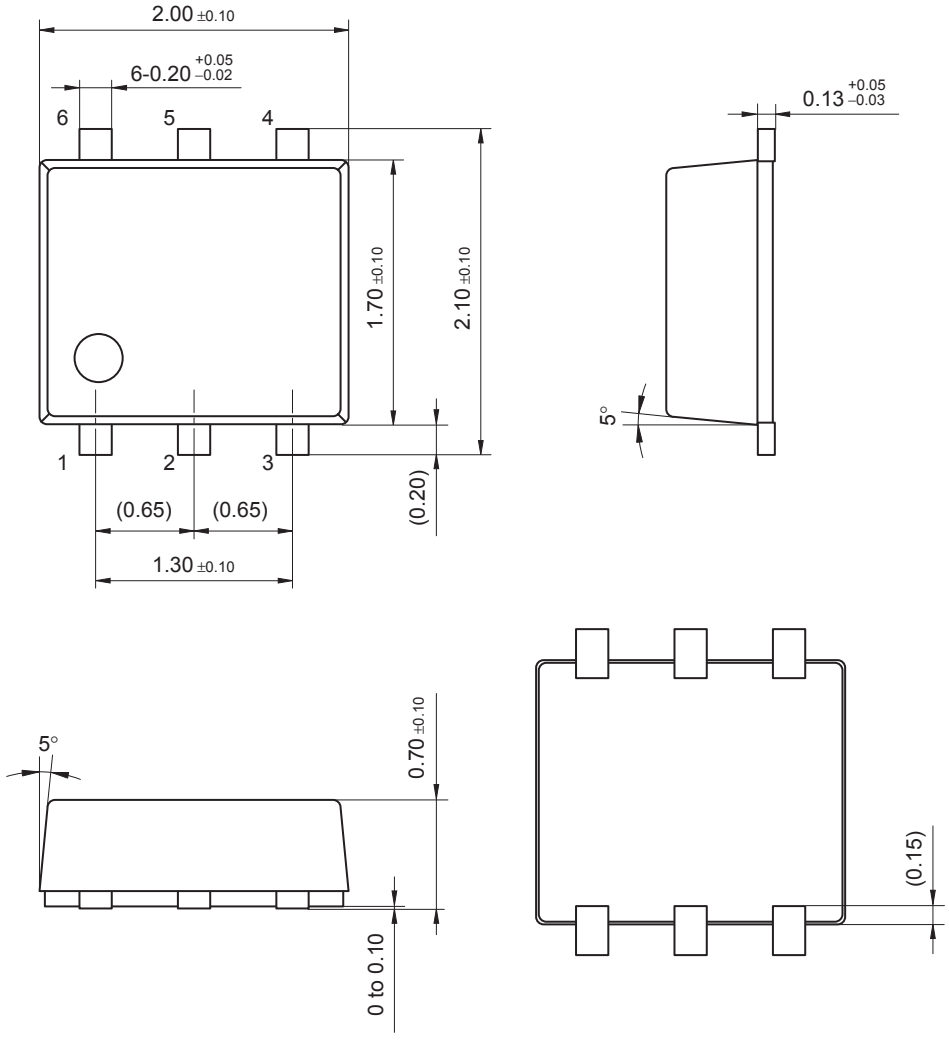


$|Y_{fs}|$ — I_D



WSMini6-F1-B

Unit: mm



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